

FIG. 2. The intensity of the 15-MeV electrons scattered in the 1.4- μm -thick silicon crystal as a function of the angle of entry θ_0 relative to the direction of the $\langle 111 \rangle$ axis. I_0 is the intensity of the incident particles. The experimental points were taken from Ref. 4; the solid curve denotes theoretical calculation.

$$\sigma = \sigma_0 + \frac{2}{\pi} \frac{L}{p} \frac{\frac{1}{4} \Gamma^2}{(E - E_{\text{res}})^2 + \frac{1}{4} \Gamma^2}; \quad \Gamma \sim E_{\text{res}} \exp - |2E_{\text{res}} V_0 R^2 - \pi^2 n^2|^{\frac{1}{2}};$$

$$E_{\text{res}} = \theta_0^{-2} \{ 2V_0 + [4V_0^2 + 4\theta_0^2 R^{-2} (\pi^2 n^2 + m^2)]^{\frac{1}{2}} \}. \quad (12)$$

The indicated resonance can be observed in the crystal when the fast particle enters it at a small angle to the crystallographic axis. In this case the longitudinal momentum transfer becomes very small $q_{\parallel} \sim 1/pR^2$ and the wave function of the particle, which is insensitive to the details of the behavior of the potential at approximately the interatomic distances, is determined by a certain potential averaged over the length of the chain.^[2] Schiebel and Worm^[4] observed the scattering of 15-MeV electrons along the $\langle 111 \rangle$ axis of a 1.4- μm -thick Si crystal. Figure 2 shows a small-angle dependence of the intensity of the scattered particles on the angle of entry relative to the crystallographic $\langle 111 \rangle$ axis. This dependence cannot be explained in terms of the usual two-wave diffraction theory and the classical string scattering.^[5] From the viewpoint of the discussion conducted above, the very narrow peak near the zero angle of entry is due to the true bound states; at the same time, its width $\sim 1/\sqrt{pL} \approx 0.02^\circ$ is very close

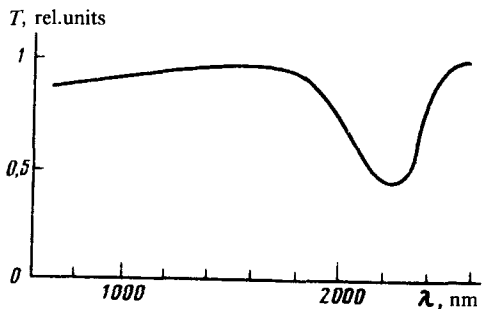


FIG. 1. Transmission spectrum of a planar texture of CLC with a pitch $P = 1.5 \mu\text{m}$.

sputtered on one of the glass plates, placed parallel to each other and spaced $300 \mu\text{m}$ apart.

The 1.5-kHz field produced a strain and a partial untwisting of the cholesteric helix, which modulated the transmission of light at a frequency $2f$. The modulation signal (variation of transmission in the field) was measured after a narrow-band amplification by a synchronous detector. The measurement circuit was described by us elsewhere.^[7]

Figure 1 shows the transmission spectrum of a planar texture of CLC at a normal

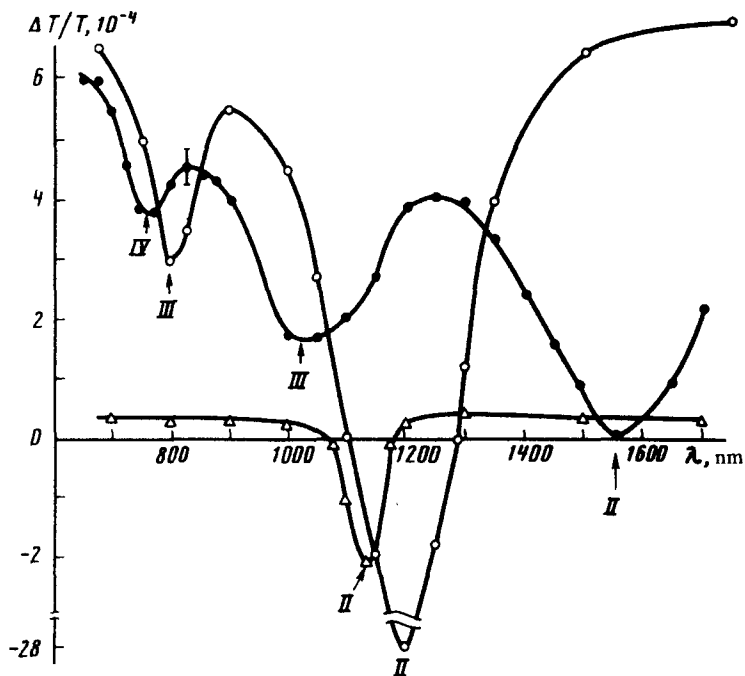


FIG. 2. Differential spectra of relative variation of the transmission $\Delta T/T$ of a sample for different voltages, U ; \triangle , $U = 200 \text{ V}$; \circ , 600 V , and \bullet , 1000 V . The Roman numerals denote the higher-order selective reflection (the first order is in the infrared region).